

1N4001 THRU 1N4007

1.0AMP . SILICON RECTIFIERS

FEATURE

- . High current capability
- . Low forward voltage drop
- . Low power loss, high efficiency
- . High surge capability
- . High temperature soldering guaranteed $260^{\circ}\text{C}\ / 10\text{sec}/\ 0.375"$ lead length at 5 lbs tension

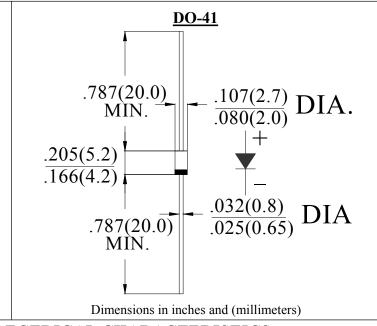
MECHANICAL DATA

. Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C

. Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy

. Polarity: color band denotes cathode

. Mounting position: any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

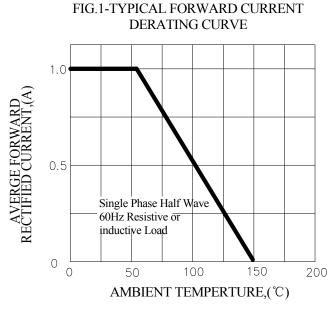
Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.

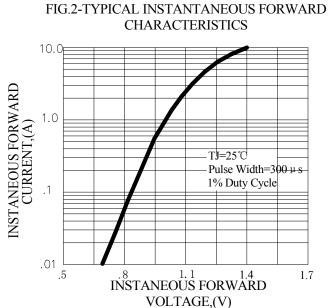
For capacitive load, derate current by 20%

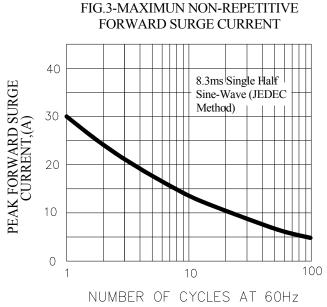
Type Number	SYM BOL	1N 4001	1N 4002	1N 4003	1N 4004	1N 4005	1N 4006	1N 4007	units
Maximum Recurrent Peak Reverse Voltage	$V_{ m RRM}$	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{ m RMS}$	35	70	140	280	420	560	700	V
Maximum DC blocking Voltage	$V_{ m DC}$	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) lead length at T _A =55°C	$I_{ m F(AV)}$	1.0							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	$I_{ m FSM}$	30.0							A
Maximum Forward Voltage at 1.0A DC	$V_{ m F}$	1.0							V
Maximum Forward Voltage at 3.0A DC	V_{F}	1.3							V
Maximum DC Reverse Current @T _A =25°C at rated DC blocking voltage @T _A =100°C	$I_{ m R}$	5.0 100.0							μΑ
Typical Junction Capacitance (Note 1)	$C_{ m J}$	15							pF
Typical Thermal Resistance (Note 2)	$R_{(JA)}$	75							°C/W
Storage Temperature	TSTG	-55 to +150							°C
Operation JunctionTemperature	$T_{ m J}$	-55 to +150							°C

Note:

- 1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
- 2. Thermal Resistance from Junction to Ambient at 0.375" (9.5mm) lead length, vertical P.C.Board Mounted.







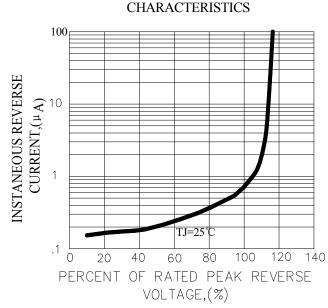


FIG.4-TYPICAL REVERSE